



Micro Commercial Components Corp.

Complete Discrete Semiconductor Solutions

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Part Number	MMBT2907A
product family	SOT-23 Plastic-Encapsulate Bipolar Transistors
Product Polarity	PNP
SMD/ThroHole	SMD
VCEO	60V
VCBO	60V
VEBO	5.0V
Ic	
PC	350mW
HFE(min)	100
@Ic	10mA
@VCE	10V
ICBO	100nA
IEBO	
VCE(sat)	0.4V
VBE(sat)	1.3V
ft	200MHz
nf	
TON_max	
Package Qty	Tape: 3K/Reel , 120K/Ctn;

Green/Pb Free/RoHS/REACH

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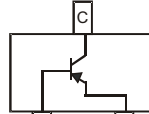
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MMBT2907A

Features

- Surface Mount SOT-23 Package
- Capable of 350mWatts of Pd, 600mA continuous collector current.
- Operating and Storage Junction Temperatures: -55°C to 150°C
- Case Material: Molded Plastic. UL Flammability Classification Rating 94-0 and MSL Rating 1
- Marking : 2F

Pin Configuration
Top View



PNP General Purpose Amplifier

Electrical Characteristics @ 25°C Unless Otherwise Specified

Symbol	Parameter	Min	Max	Units
OFF CHARACTERISTICS				
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage* ($I_C=10mA$, $I_B=0$)	60		Vdc
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage ($I_C=10\mu A$, $I_E=0$)	60		Vdc
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage ($I_E=10\mu A$, $I_C=0$)	5.0		Vdc
I_{BL}	Base Cutoff Current ($V_{CE}=30Vdc$, $V_{BE}=0.5Vdc$)		50	nAdc
I_{CEX}	Collector Cutoff Current ($V_{CE}=30Vdc$, $V_{BE}=0.5Vdc$)		50	nAdc
I_{CBO}	Collector Cutoff Current ($V_{CB}=50Vdc$, $I_E=0$) ($V_{CB}=50Vdc$, $I_E=0$, $T_A=150^\circ C$)		0.1 10.0	μA dc

ON CHARACTERISTICS

h_{FE}	DC Current Gain* ($I_C=0.1mA$, $V_{CE}=10Vdc$) ($I_C=1.0mA$, $V_{CE}=10Vdc$) ($I_C=10mA$, $V_{CE}=10Vdc$) ($I_C=150mA$, $V_{CE}=10Vdc$) ($I_C=500mA$, $V_{CE}=10Vdc$)	75 100 100 100 50	300	
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage ($I_C=150mA$, $I_B=15mA$) ($I_C=500mA$, $I_B=50mA$)		0.4 1.6	Vdc
$V_{BE(sat)}$	Base-Emitter Saturation Voltage ($I_C=150mA$, $I_B=15mA$) ($I_C=500mA$, $I_B=50mA$)		1.3 2.6	Vdc

SMALL-SIGNAL CHARACTERISTICS

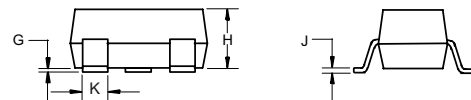
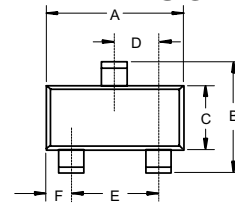
f_T	Current Gain-Bandwidth Product ($I_C=50mA$, $V_{CE}=20Vdc$, $f=100MHz$)	200		MHz
C_{cbo}	Output Capacitance ($V_{CB}=10Vdc$, $I_E=0$, $f=1.0MHz$)		8.0	pF
C_{ibo}	Input Capacitance ($V_{EB}=2.0Vdc$, $I_C=0$, $f=1.0MHz$)		30.0	pF

SWITCHING CHARACTERISTICS

t_d	Delay Time	$(V_{CC}=3.0Vdc, I_C=150mA, I_{B1}=15mA)$	10	ns
t_r	Rise Time	$(V_{CC}=3.0Vdc, I_C=150mA, I_{B1}=15mA)$	40	ns
t_s	Storage Time	$(V_{CC}=3.0Vdc, I_C=150mA, I_{B1}=I_{B2}=15mA)$	80	ns
t_f	Fall Time	$(V_{CC}=3.0Vdc, I_C=150mA, I_{B1}=I_{B2}=15mA)$	30	ns

*Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2.0\%$

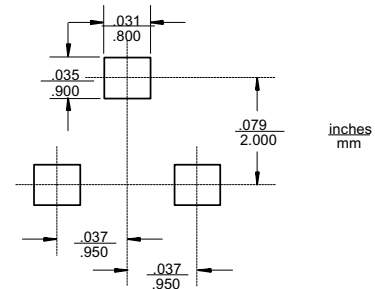
SOT-23



DIMENSIONS

DIM	INCHES		MM		NOTE
	MIN	MAX	MIN	MAX	
A	.110	.120	2.80	3.04	
B	.083	.098	2.10	2.64	
C	.047	.055	1.20	1.40	
D	.035	.041	.89	1.03	
E	.070	.081	1.78	2.05	
F	.018	.024	.45	.60	
G	.0005	.0039	.013	.100	
H	.035	.044	.89	1.12	
J	.003	.007	.085	.180	
K	.015	.020	.37	.51	

Suggested Solder Pad Layout





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Ordering Information

Device	Packing
(Part Number)-TP	Tape&Reel;3Kpcs/Reel